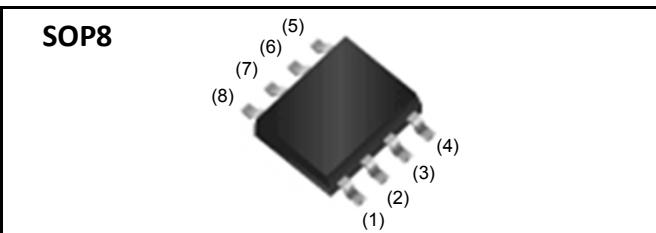


$V_{DSS}$	-30V
$R_{DS(on)}$ (Max.)	21mΩ
$I_D$	-7.5A
$P_D$	2.0W

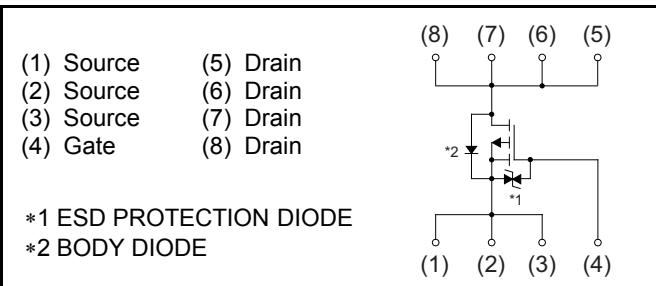
### ●Features

- 1) Low on - resistance.
- 2) Built-in G-S Protection Diode.
- 3) Small Surface Mount Package (SOP8).
- 4) Pb-free lead plating ; RoHS compliant

### ●Outline



### ●Inner circuit



### ●Packaging specifications

Type	Packaging	Taping
	Reel size (mm)	330
	Tape width (mm)	12
	Basic ordering unit (pcs)	2,500
	Taping code	TB
	Marking	RRH075P03

### ●Absolute maximum ratings( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Drain - Source voltage	$V_{DSS}$	-30	V
Continuous drain current	$I_D$ <sup>*1</sup>	$\pm 7.5$	A
Pulsed drain current	$I_{D,pulse}$ <sup>*2</sup>	$\pm 30$	A
Gate - Source voltage	$V_{GSS}$	$\pm 20$	V
Avalanche energy, single pulse	$E_{AS}$ <sup>*3</sup>	0.5	mJ
Power dissipation	$P_D$ <sup>*4</sup>	2.0	W
	$P_D$ <sup>*5</sup>	0.65	W
Junction temperature	$T_j$	150	°C
Range of storage temperature	$T_{stg}$	-55 to +150	°C

### ● Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - ambient	$R_{thJA}$ <sup>*4</sup>	-	-	62.5	°C/W
Thermal resistance, junction - ambient	$R_{thJA}$ <sup>*5</sup>	-	-	192	°C/W

### ● Electrical characteristics ( $T_a = 25^\circ C$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = -1mA$	-30	-	-	V
Breakdown voltage temperature coefficient	$\frac{\Delta V_{(BR)DSS}}{\Delta T_j}$	$I_D = -1mA$ referenced to $25^\circ C$	-	-25	-	mV/°C
Zero gate voltage drain current	$I_{DSS}$	$V_{DS} = -30V, V_{GS} = 0V$	-	-	-1	μA
Gate - Source leakage current	$I_{GSS}$	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 10$	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{DS} = -10V, I_D = -1mA$	-1	-	-2.5	V
Gate threshold voltage temperature coefficient	$\frac{\Delta V_{(GS)th}}{\Delta T_j}$	$I_D = -1mA$ referenced to $25^\circ C$	-	3.9	-	mV/°C
Static drain - source on - state resistance	$R_{DS(on)}^{*6}$	$V_{GS} = -10V, I_D = -7.5A$	-	15	21	mΩ
		$V_{GS} = -4.5V, I_D = -4A$	-	22	31	
		$V_{GS} = -4.0V, I_D = -4A$	-	25	35	
		$V_{GS} = -10V, I_D = -7.5A, T_j = 125^\circ C$	-	23	33	
Gate input resistancce	$R_G$	f = 1MHz, open drain	-	4	-	Ω
Transconductance	$g_{fs}^{*6}$	$V_{DS} = -10V, I_D = -7.5A$	9	18	-	S

\*1 Limited only by maximum temperature allowed.

\*2  $P_w \leq 10\mu s$ , Duty cycle  $\leq 1\%$

\*3  $L \approx 10\mu H$ ,  $V_{DD} = -15V$ ,  $R_g = 25\Omega$ , starting  $T_j = 25^\circ C$

\*4 Mounted on a seramic board (30×30×0.8mm)

\*5 Mounted on a FR4 (20×20×0.8mm)

●Electrical characteristics( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ $V_{DS} = -10\text{V}$ $f = 1\text{MHz}$	-	1900	-	pF
Output capacitance	$C_{oss}$		-	250	-	
Reverse transfer capacitance	$C_{rss}$		-	250	-	
Turn - on delay time	$t_{d(on)}^{\ast 6}$	$V_{DD} \approx -15\text{V}, V_{GS} = -10\text{V}$ $I_D = -4\text{A}$ $R_L = 3.8\Omega$ $R_G = 10\Omega$	-	14	-	ns
Rise time	$t_r^{\ast 6}$		-	25	-	
Turn - off delay time	$t_{d(off)}^{\ast 6}$		-	100	-	
Fall time	$t_f^{\ast 6}$		-	70	-	

●Gate Charge characteristics( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	$Q_g^{\ast 6}$	$V_{DD} \approx -15\text{V}, I_D = -7.5\text{A}$ $V_{GS} = -5\text{V}$	-	21	-	nC
		$V_{DD} \approx -15\text{V}, I_D = -7.5\text{A}$ $V_{GS} = -10\text{V}$	-	41	-	
Gate - Source charge	$Q_{gs}^{\ast 6}$	$V_{DD} \approx -15\text{V}, I_D = -7.5\text{A}$ $V_{GS} = -5\text{V}$	-	5	-	
Gate - Drain charge	$Q_{gd}^{\ast 6}$		-	7	-	

●Body diode electrical characteristics (Source-Drain)( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Inverse diode continuous, forward current	$I_S^{\ast 1}$	$T_a = 25^\circ\text{C}$	-	-	-1.6	A
Forward voltage	$V_{SD}^{\ast 6}$	$V_{GS} = 0\text{V}, I_s = -7.5\text{A}$	-	-	-1.2	V
Reverse recovery time	$t_{rr}^{\ast 6}$	$I_S = -7.5\text{A}$ $di/dt = 100\text{A} / \mu\text{s}$	-	30	60	ns
Reverse recovery charge	$Q_{rr}^{\ast 6}$		-	20	40	$\mu\text{C}$

\*6 Plused

## ●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

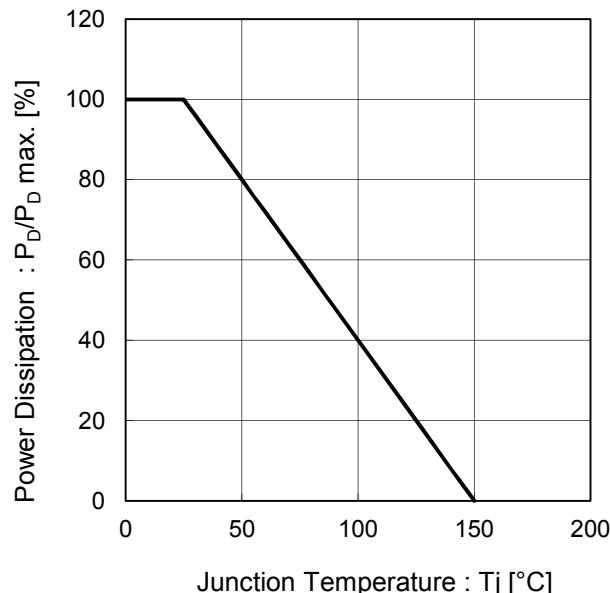


Fig.2 Maximum Safe Operating Area

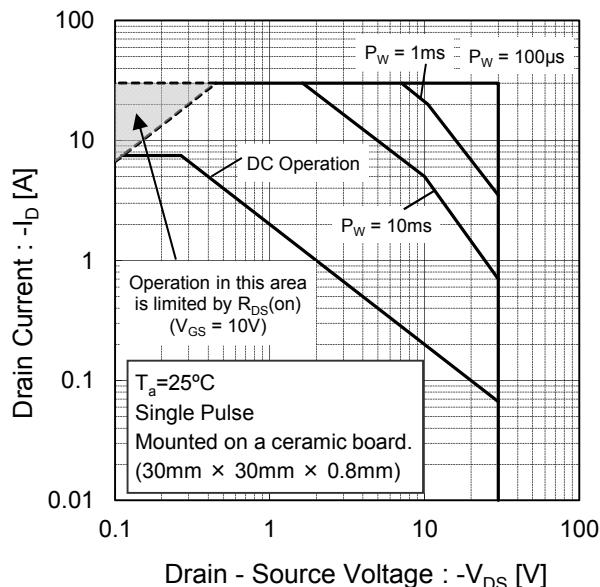


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width

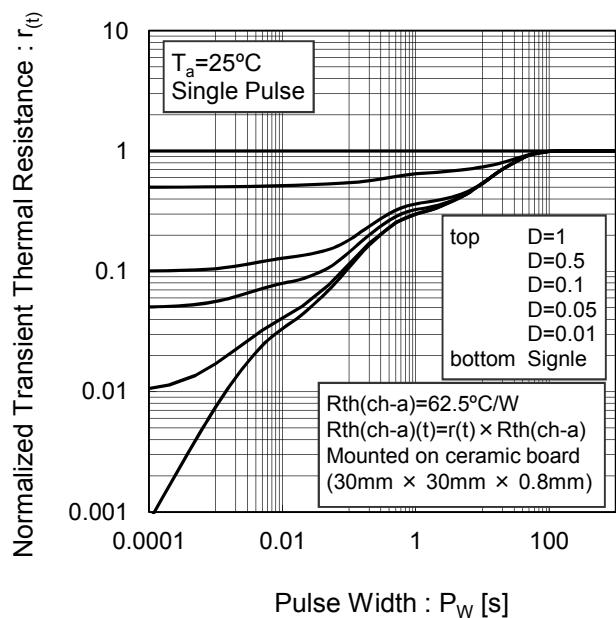
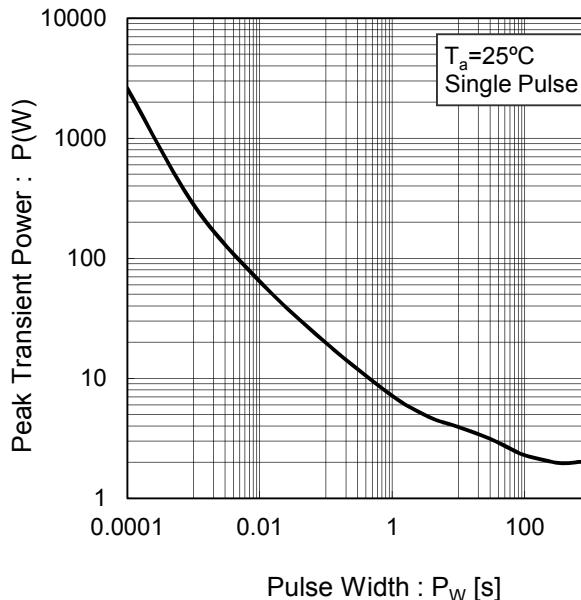


Fig.4 Single Pulse Maximum Power dissipation



● Electrical characteristic curves

Fig.5 Avalanche Current vs Inductive Load

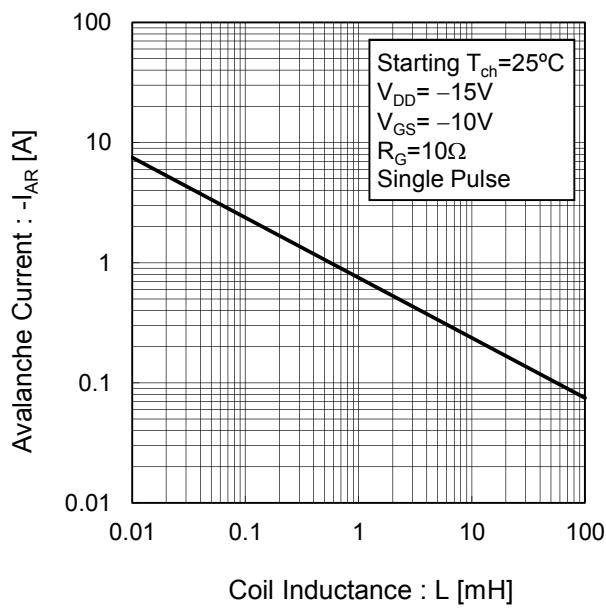


Fig.6 Avalanche Energy Derating Curve vs Junction Temperature

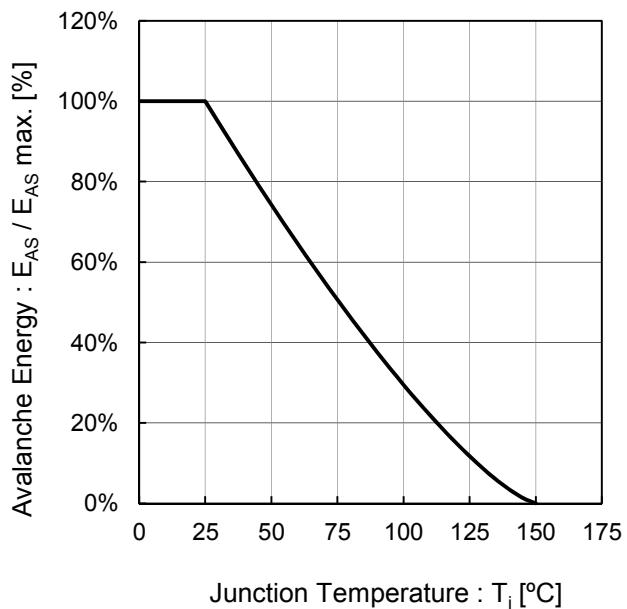


Fig.7 Typical Output Characteristics(I)

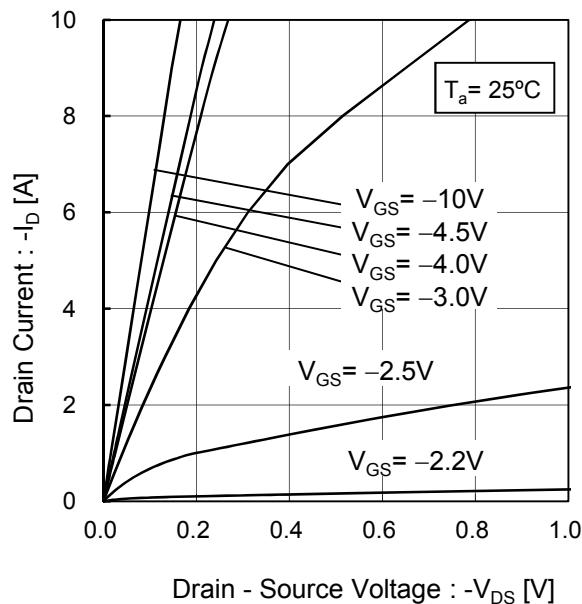
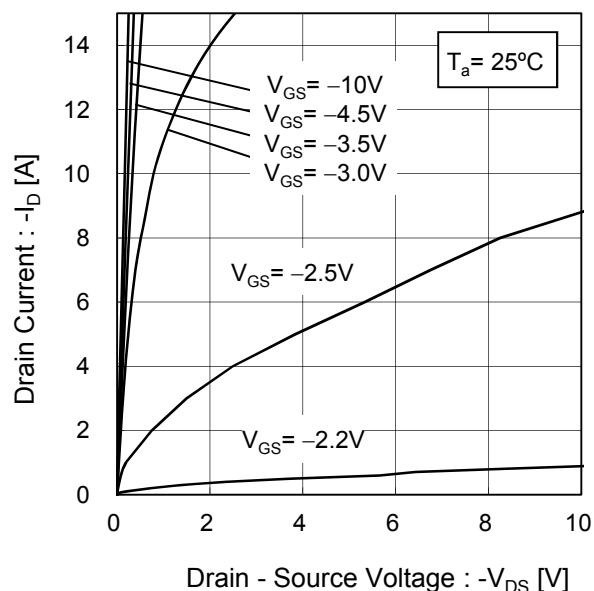


Fig.8 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.9 Breakdown Voltage  
vs. Junction Temperature

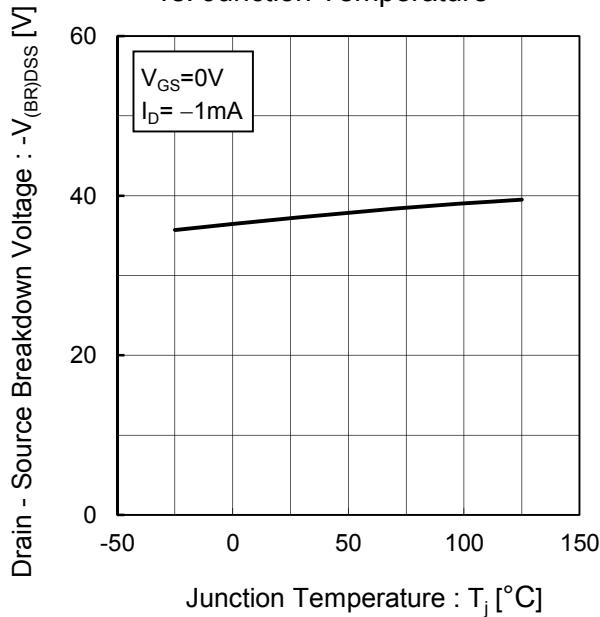


Fig.10 Typical Transfer Characteristics

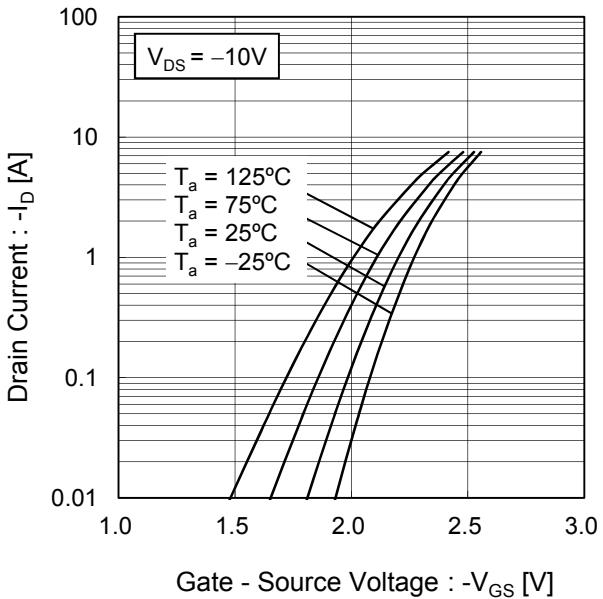


Fig.11 Gate Threshold Voltage  
vs. Junction Temperature

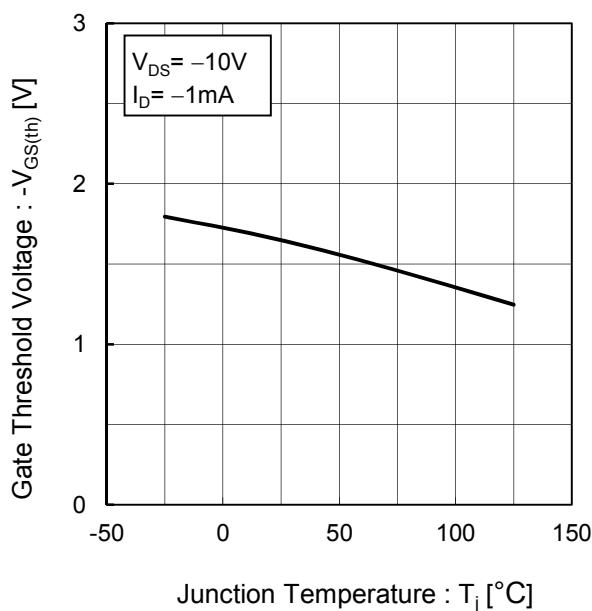
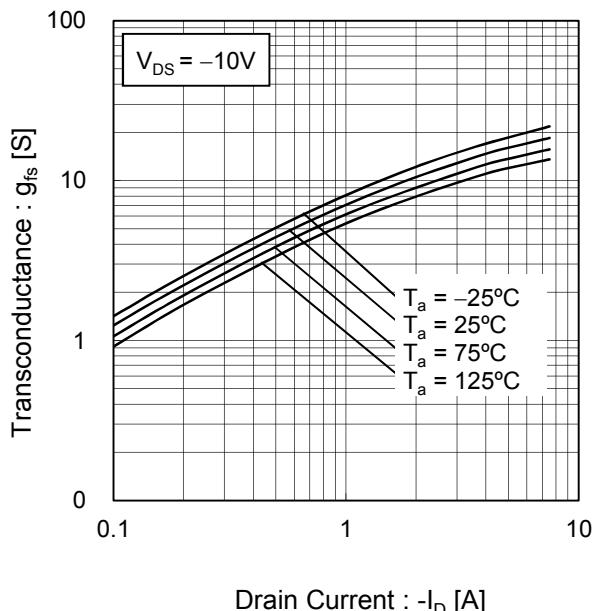


Fig.12 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.13 Drain CurrentDerating Curve

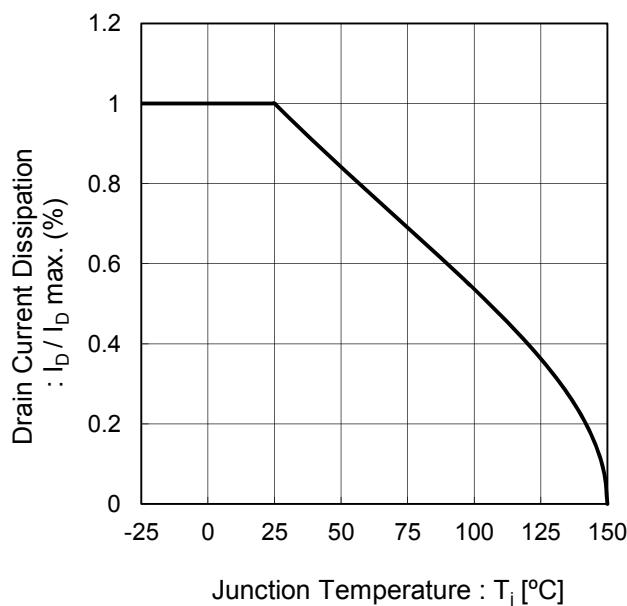


Fig.14 Static Drain - Source On - State Resistance vs. Gate Source Voltage

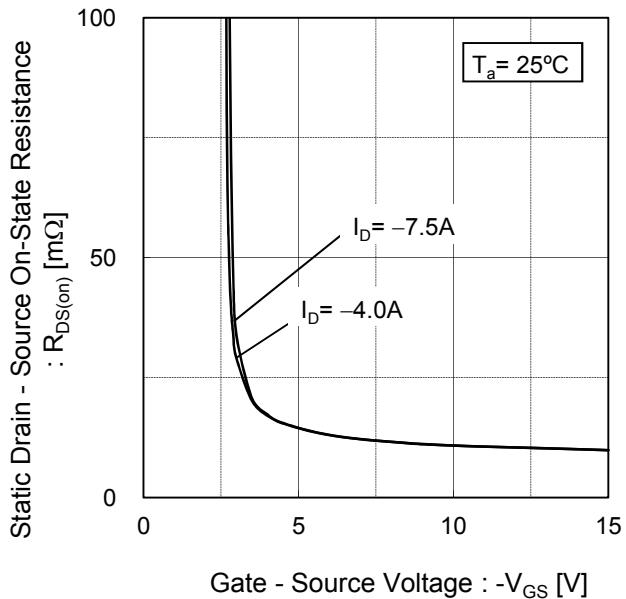


Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I)

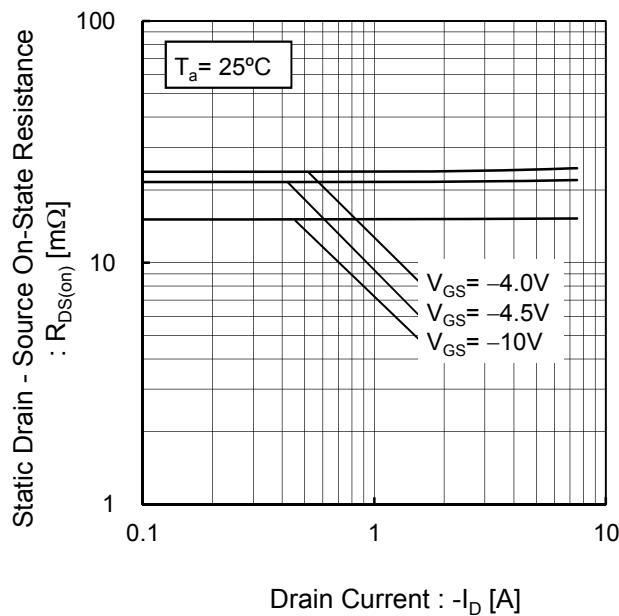
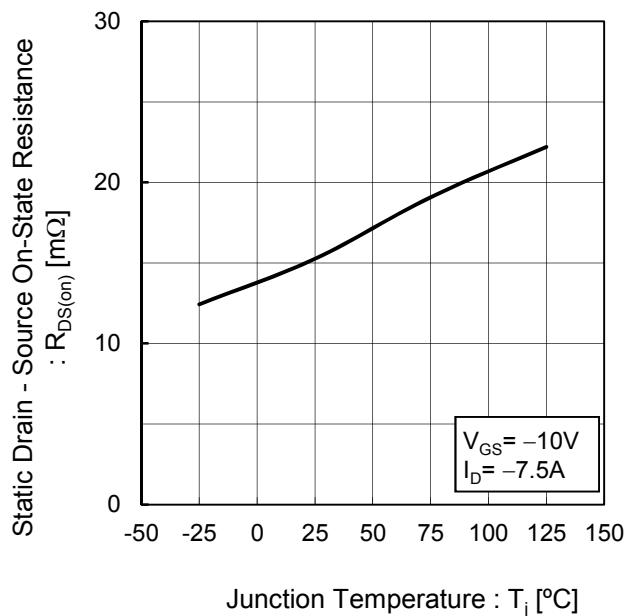


Fig.16 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.17 Static Drain - Source On - State Resistance vs. Drain Current(II)

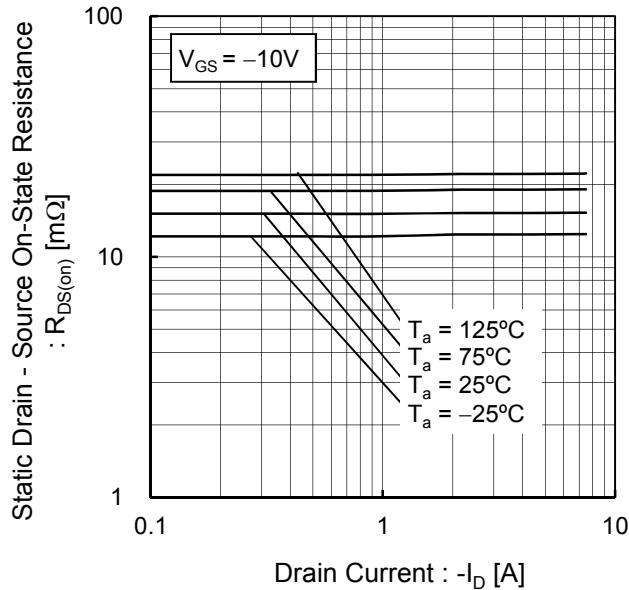


Fig.18 Static Drain - Source On - State Resistance vs. Drain Current(III)

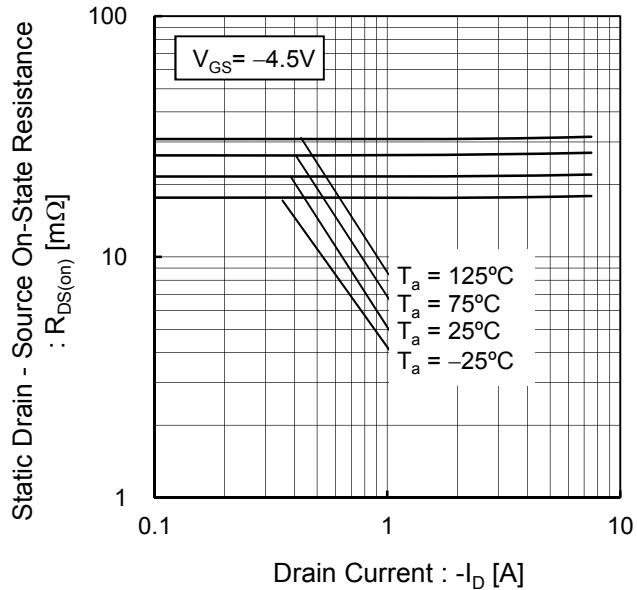
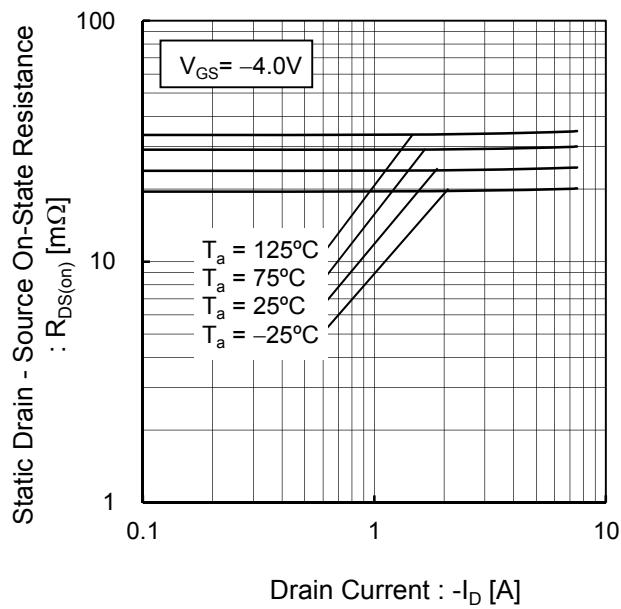


Fig.19 Static Drain - Source On - State Resistance vs. Drain Current(IV)



● Electrical characteristic curves

Fig.20 Typical Capacitance vs. Drain - Source Voltage

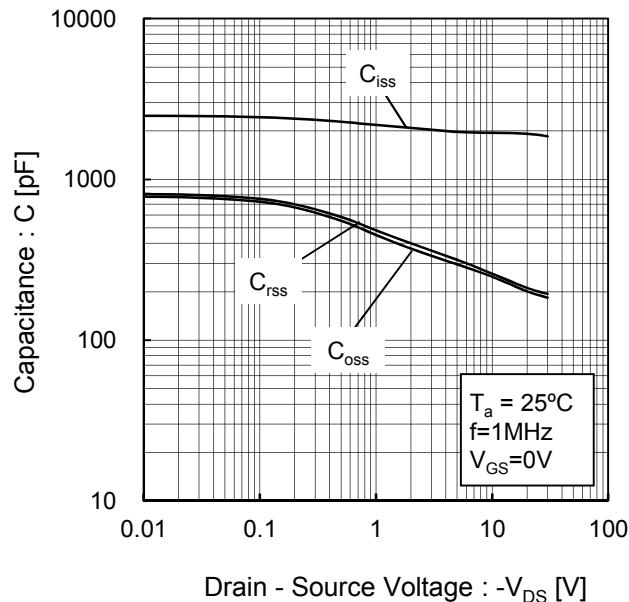


Fig.21 Switching Characteristics

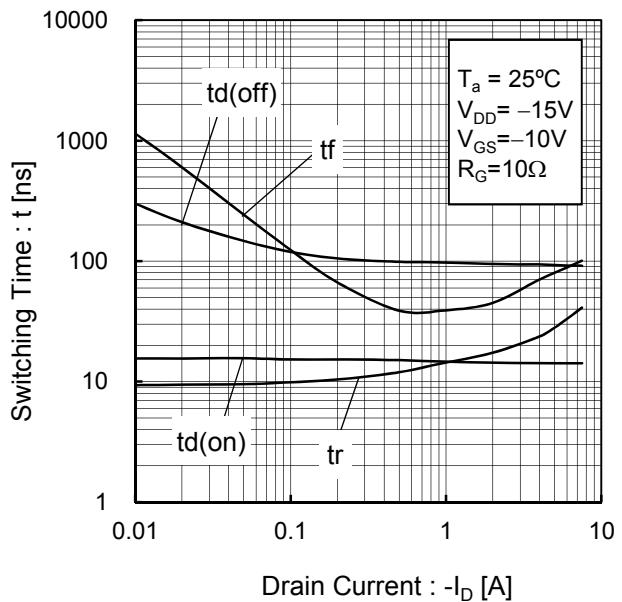


Fig.22 Dynamic Input Characteristics

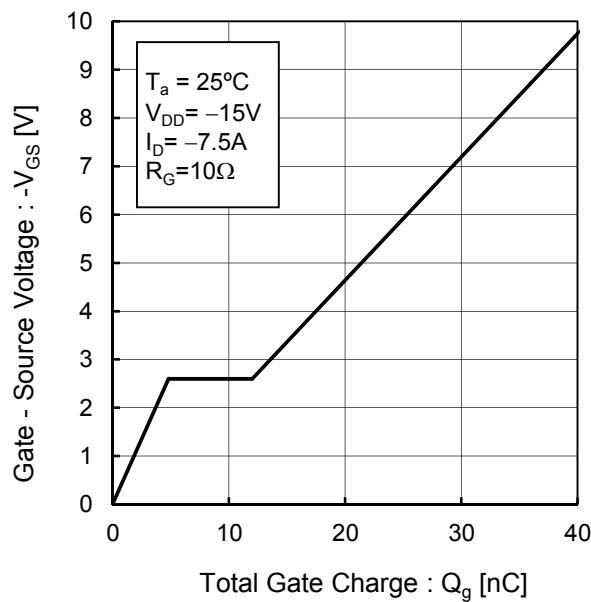
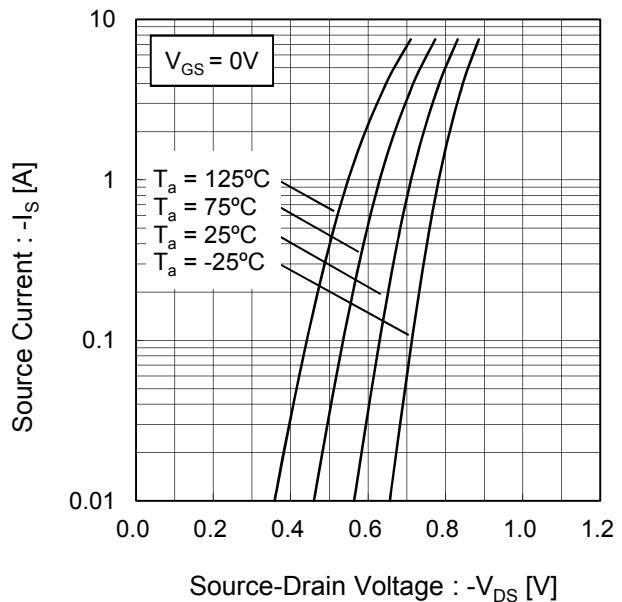


Fig.23 Source Current vs. Source Drain Voltage



## ●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

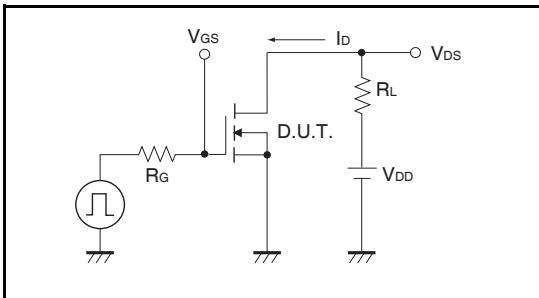


Fig.1-2 Switching Waveforms

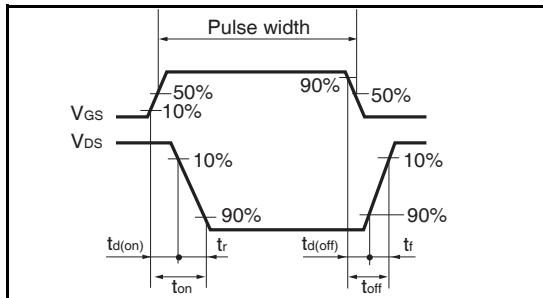


Fig.2-1 Gate Charge Measurement Circuit

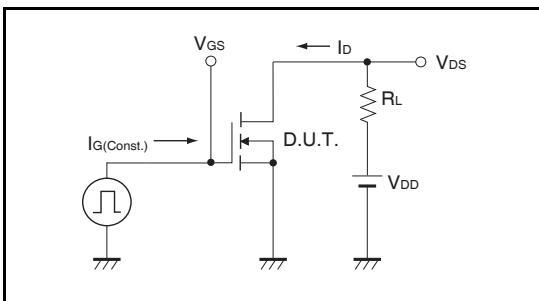


Fig.2-2 Gate Charge Waveform

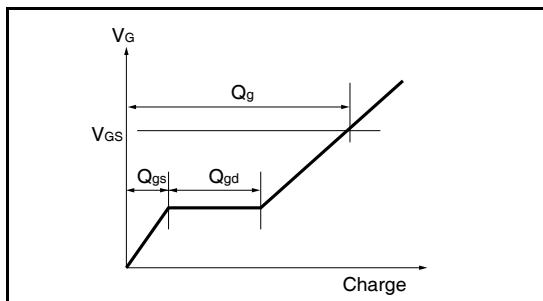


Fig.3-1 Avalanche Measurement Circuit

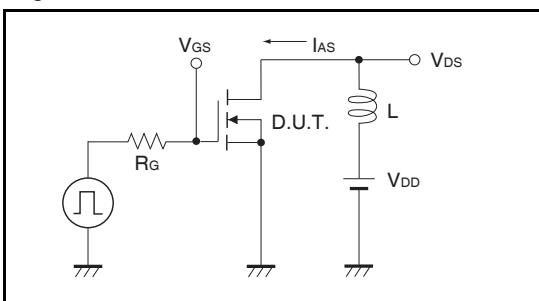
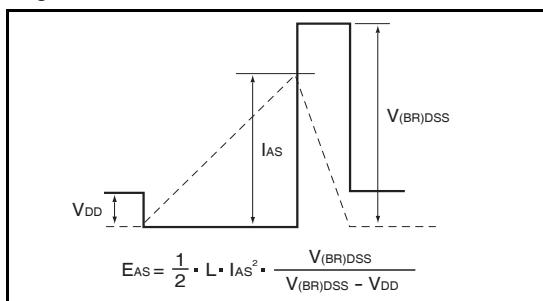
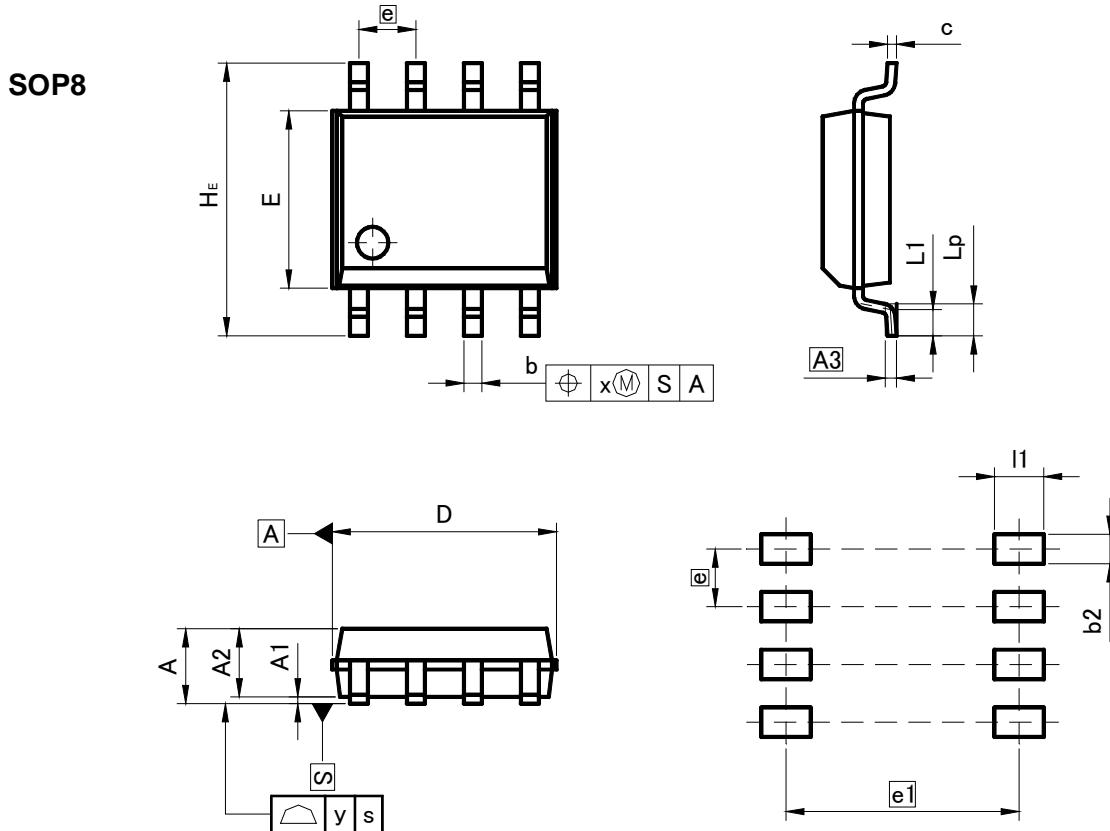


Fig.3-2 Avalanche Waveform



●Dimensions (Unit : mm)



Pattern of terminal position areas

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	-	1.75	-	0.069
A1	0.15		0.006	
A2	1.40	1.60	0.055	0.063
A3	0.25		0.01	
b	0.30	0.50	0.012	0.02
c	0.10	0.30	0.004	0.012
D	4.80	5.20	0.189	0.205
E	3.75	4.05	0.148	0.159
e	1.27		0.05	
$H_E$	5.70	6.30	0.224	0.248
$L_1$	0.50	0.70	0.02	0.028
$L_p$	0.65	0.85	0.026	0.033
x	0.15		0.006	
y	0.10		0.004	

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
$b_2$	-	0.65	-	0.026
$e_1$	5.15		0.203	
$I_1$	-	1.15	-	0.045

Dimension in mm/inches

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